SemTron Microtech Corporation

STN3400A

30V N-Channel Enhancement Mode MOSFET

N-Channel Enhancement Mode MOSFET

DESCRIPTION

The STN3400A is the N-Channel logic enhancement mode power field effect transistor is produced using high cell density. advanced trench technology to provide excellent R_{DS}(ON).low gate charge and operation gate as 2.5V.
This device is suitable for use as a load switch or other general applications.

STN3400AS-TRG ROHS Compliant This is Halogen Free

FEATURE

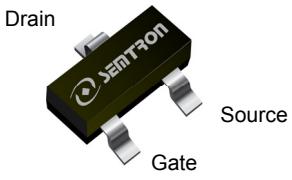
- ***30V/5.6A, $R_{DS(ON)}$ =28mΩ(typ.)@V_{GS} =10V***
- ***30V/5.0A, $R_{DS(ON)}$ =30mΩ(typ.)@V_{GS} =4.5V***
- ***30V/3.2A, $R_{DS(ON)}$ =35mΩ(typ.)@V_{GS} =2.5V***
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and Maximum DC current capability

APPLICATIONS

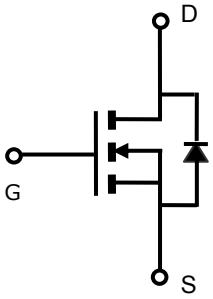
- Power Management in Note book
- Portable Equipment
- DSC
- LCD Display inverter
- Battery Powered System
- DC/DC Converter

Green Product

PIN CONFIGURATION



SOT-23
Top View



PART NUMBER INFORMATION

ST N 3400A S - TR G a b c d e f	**a : Company name.** **b : Channel type.** **c : Product Serial number.** **d : Package code** **e : Handling code** **f : Green product code**

■ORDERING INFORMATION

Part Number	Package Code	Handling Code	Shipping
STN3400AS-TRG	S : SOT-23	TR : Tape&Reel	3K/Reel

※ Year Code : 0 ~ 9, 2010 : 0
※ Week Code : A(1~2) ~ Z(53~54)
※ SOT-23L : Only available in tape and reel packaging.

■ABSOLUTE MAXIMUM RATINGS (T_A = 25℃ Unless otherwise noted)

Symbol	Parameter		Typical	Unit
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±12	V
I_D	Continuous Drain Current (T_C=25°C) [A]	V_{GS}=10V	5.6	A
	Continuous Drain Current (T_C=70°C) [A]		5.0	A
I_{DM}	Pulsed Drain Current [B]		20	A
P_D	Power Dissipation	T_A=25°C T_A=70°C	1.0 0.7	W
T_J	Operation Junction Temperature		-55 to150	°C
T_{STG}	Storage Temperature Range		-55 to150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■THERMAL DATA

Symbol	Parameter		Typ	Max	Unit
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient [A]	Steady-State	-	120	°C/W
$R_{\theta JL}$	Thermal Resistance Junction to Lead [A]	Steady-State	-	85	°C/W

■ELECTRICAL CHARACTERISTICS(T_J = 25℃ Unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=250μA	30			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	0.6		1.2	V
I_{GSS}	Gate Leakage Current	V_{DS}=0V,V_{GS}=±12V			±100	nA
I_{DSS}	Zero Gate Voltage, Drain-Source Leakage Current	V_{DS}=24V,V_{GS}=0V T_J=25°C			1	μA
		V_{DS}=24V,V_{GS}=0V T_J=55°C			5	
$R_{DS(ON)}$	Drain-source On-Resistance[B]	V_{GS}=10V,I_D=5.6A V_{GS}=4.5V,I_D=5.0A V_{GS}=2.5V,I_D=3.2A		28 30 35	33 35 40	mΩ
G_{fs}	Forward Transconductance	V_{DS}=15V,I_D=5.0A		12		S
R_g	Gate Resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		1.5	3	Ω
Source-Drain Doide						
V_{SD}	Diode Forward Voltage	I_S=1.0A,V_{GS}=0V		0.7	1.0	V
I_S	Continuous Source Current[AD]				5.8	A
Dynamic Parameters						
Q_g (4.5V)	Total Gate Charge	V_{DS}=20V V_{GS}=4.5V I_D≡5.8A		8.65		nC
Q_{gs}	Gate-Source Charge			1.26		
Q_{gd}	Gate-Drain Charge			1.85		
C_{iss}	Input Capacitance	V_{DS}=15V V_{GS}=0V f=1MHz		468		pF
C_{oss}	Output Capacitance			52.5		
C_{rss}	Reverse Transfer Capacitance			43.2		
$t_{d(on)}$	Turn-On Time	V_{DD}=15V I_D=4A V_{GEN}=10V R_G=3.3Ω		3.3	6.5	nS
t_r				42	77	
$t_{d(off)}$	Turn-Off Time			22	43	
t_f				6.5	13	

Note:

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

B. The data tested by pulsed , pulse width ≦ 300uS , duty cycle ≦ 2%

C. The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH.

D. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

The products and product specifications contained herein are subject to change without notice to improve performance characteristics. Consult us, or our representatives before use, to confirm that the information in this datasheet is up to date

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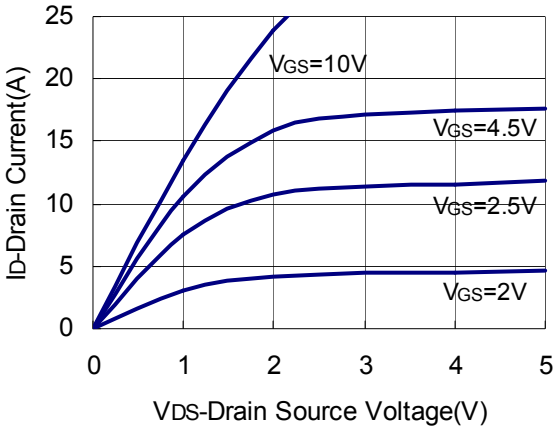
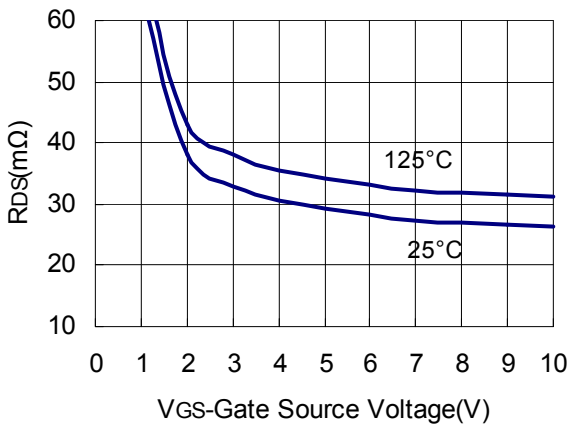
TYPICAL CHARACTERISTICS (25℃ Unless Note)

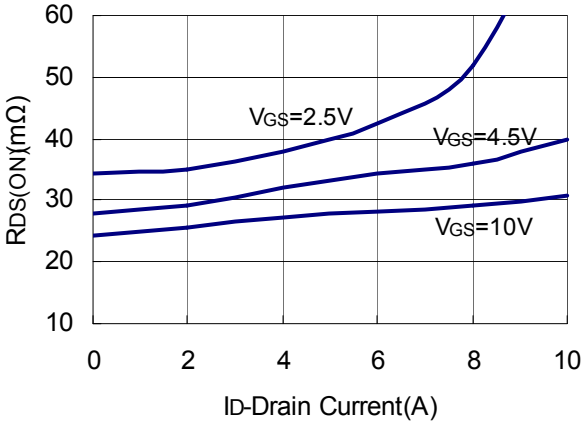
Output Characteristics



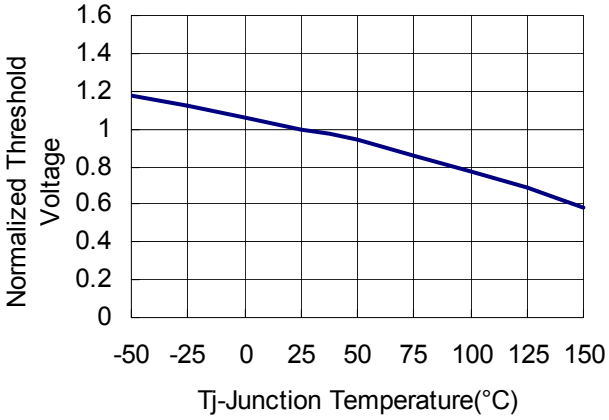
Drain-Source On Resistance



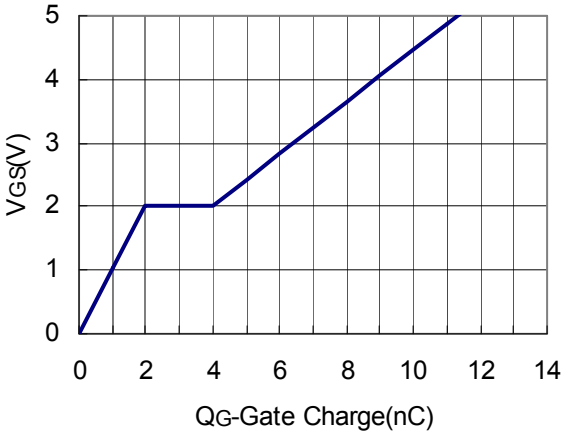
Drain Source On Resistance



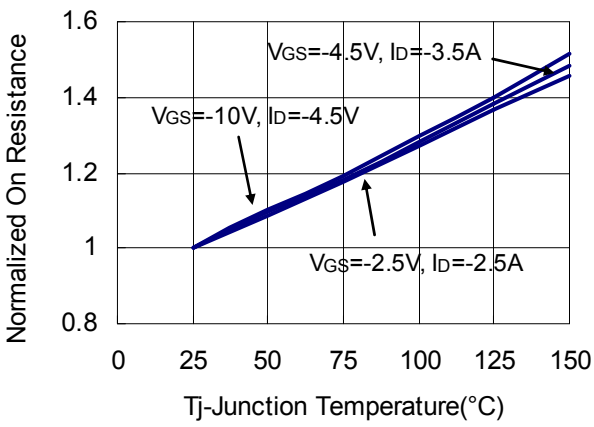
Gate Threshold Voltage



Gate Charge

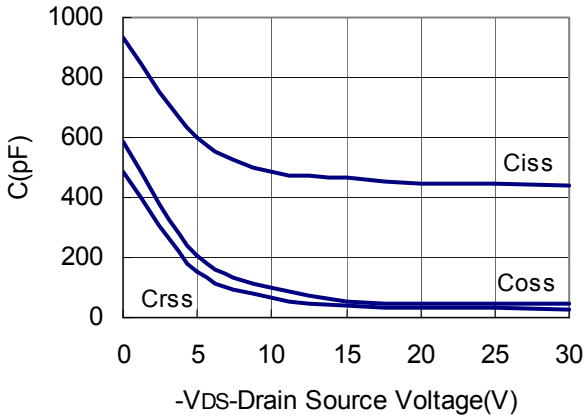


Drain Source Resistance

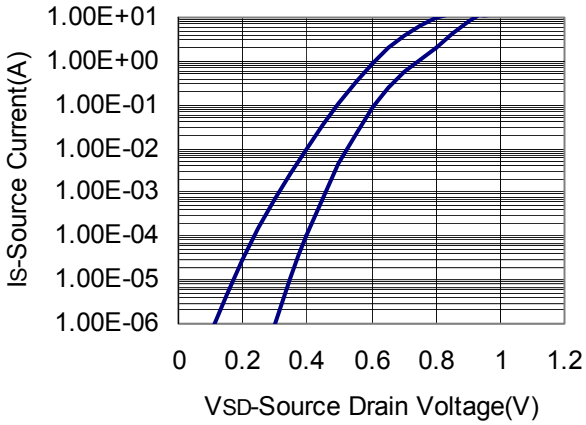


TYPICAL CHARACTERISTICS (25℃ Unless Note)

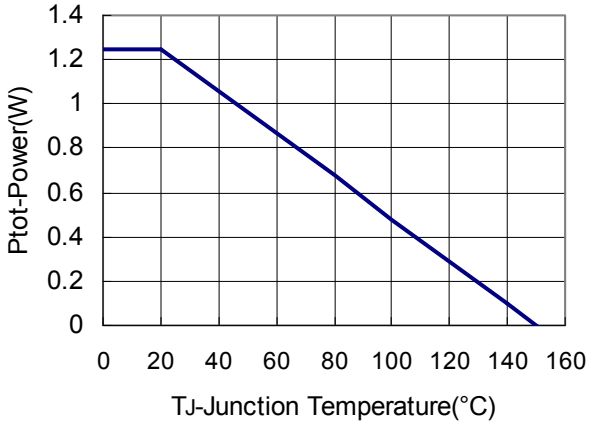
Capacitance



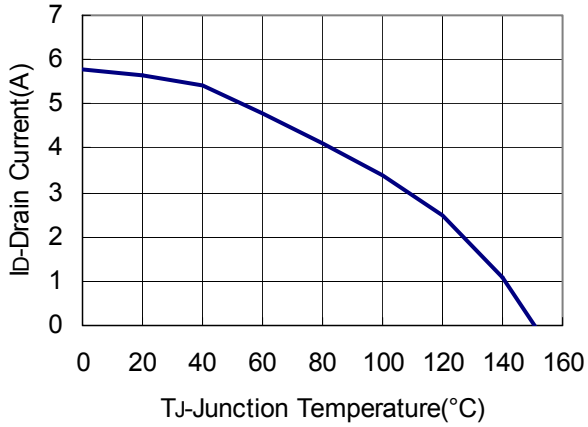
Source Drain Diode Forward



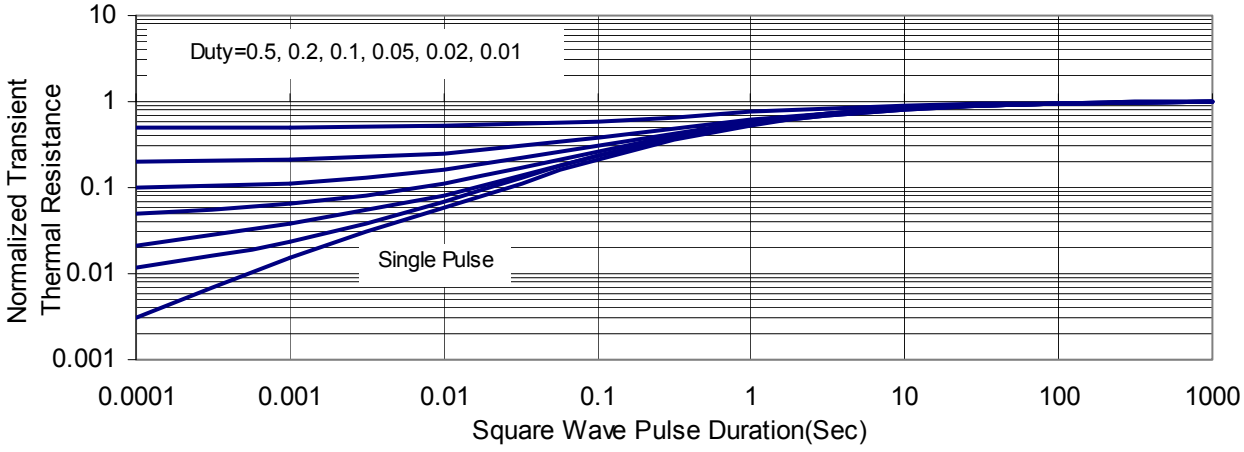
Power Dissipation



Drain Current



Thermal Transient Impedance



SOT-23 PACKAGE DIMENSIONS

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L1	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°